	Туре	L#	Hits	Search Text	DBs	Time Stamp	o m m e	ef	Er ro rs
1	BRS	L1	0	clean\$3 same ("polyoeyethylene butyphel ether")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 19:19			0
2	BRS	L2	783	clean\$3 same ("polyoeyethylene butylphenyl ether") or( polyoxyethylene with phenyl with sulfate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 19:20	-		0
3	BRS	L3	16	clean\$3 same (("polyoeyethylene butylphenyl ether") or (polyoxyethylene with phenyl with sulfate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 19:24			0
4	BRS	L4	0	"20020202852"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 19:24			0
5	BRS	L5	2	"20020102852"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 19:38			0
6	BRS	L6	62192	thermal with (anneal\$3 or (cvd or "chemicl vapor deposition") or (oxidation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 19:40			0
7	BRS	L7	38560	6 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 19:40			0
8	BRS	L8	101	thermal with (anneal\$3 with (cvd or "chemicl vapor deposition") with (oxidation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 19:40		•	0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	C o m e nt s	r D ef in iti	E
9	BRS	L9	98	8 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 19:41			0
10	BRS	L10	40	9 and @pd<=20000626	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/17 19:41			0

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